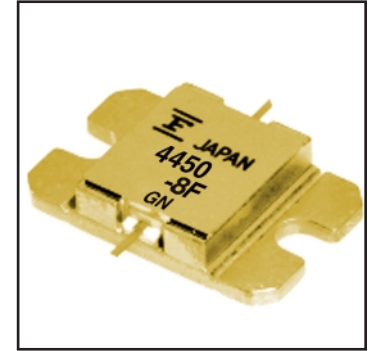


FEATURES

- High Output Power: $P_{1dB} = 39.5dBm$ (Typ.)
- High Gain: $G_{1dB} = 10.0dB$ (Typ.)
- High PAE: $\eta_{add} = 36%$ (Typ.)
- Low $IM_3 = -46dBc@P_o = 28.5dBm$
- Broad Band: 4.4 ~ 5.0GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package



DESCRIPTION

The FLM4450-8F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ C$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_C = 25^\circ C$	42.8	W
Storage Temperature	T_{stg}		-65 to +175	$^\circ C$
Channel Temperature	T_{ch}		175	$^\circ C$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 32.0 and -4.4 mA respectively with gate resistance of 100 Ω .

ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ C$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS} = 5V, V_{GS} = 0V$	-	3900	5850	mA
Transconductance	g_m	$V_{DS} = 5V, I_{DS} = 2200mA$	-	2000	-	mS
Pinch-off Voltage	V_p	$V_{DS} = 5V, I_{DS} = 180mA$	-1.0	-2.0	-3.5	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS} = -180\mu A$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS} = 10V,$ $I_{DS} = 0.55 I_{DSS}$ (Typ.), $f = 4.4 \sim 5.0$ GHz, $Z_S = Z_L = 50$ ohm	38.5	39.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		9.0	10.0	-	dB
Drain Current	I_{dsr}		-	2200	2600	mA
Power-added Efficiency	η_{add}		-	36	-	%
Gain Flatness	ΔG		-	-	± 0.6	dB
3rd Order Intermodulation Distortion	IM_3	$f = 5.0$ GHz, $\Delta f = 10$ MHz 2-Tone Test $P_{out} = 28.5dBm$ S.C.L.	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	3.0	3.5	$^\circ C/W$
Channel Temperature Rise	ΔT_{ch}	$10V \times I_{dsr} \times R_{th}$	-	-	80	$^\circ C$

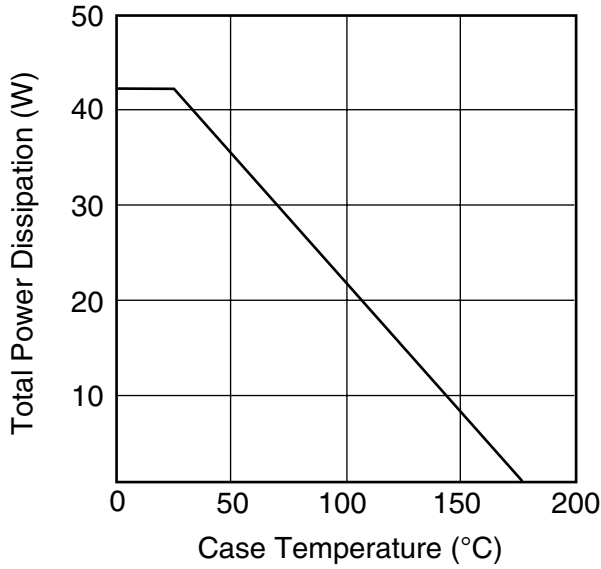
CASE STYLE: IB

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

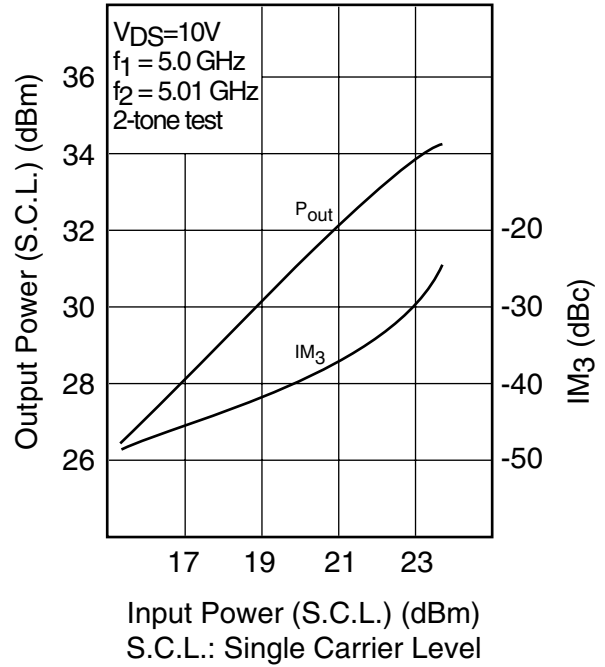
FLM4450-8F

C-Band Internally Matched FET

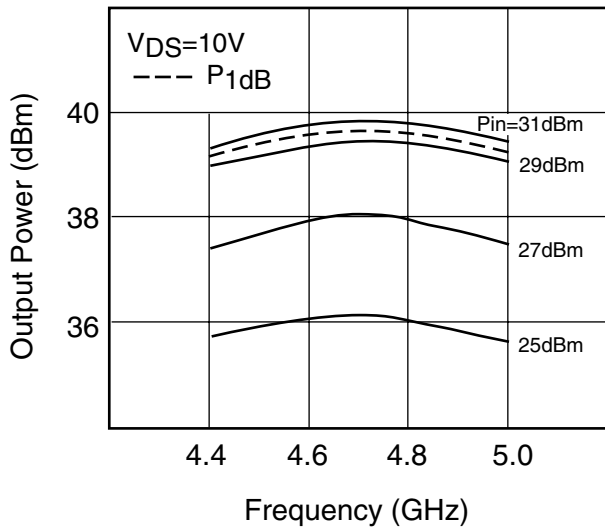
POWER DERATING CURVE



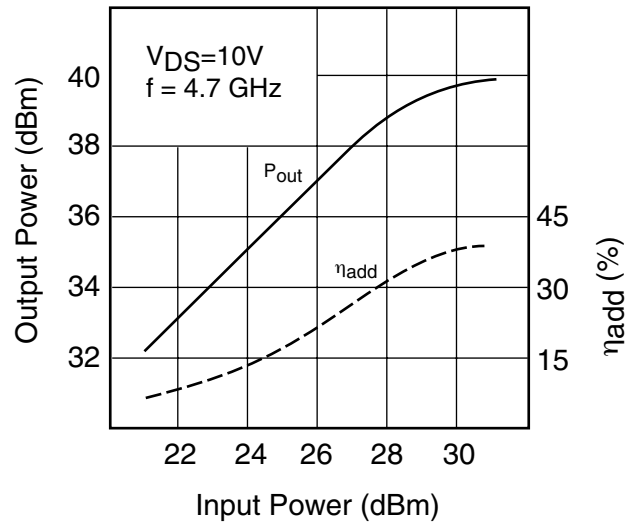
OUTPUT POWER & IM₃ vs. INPUT POWER

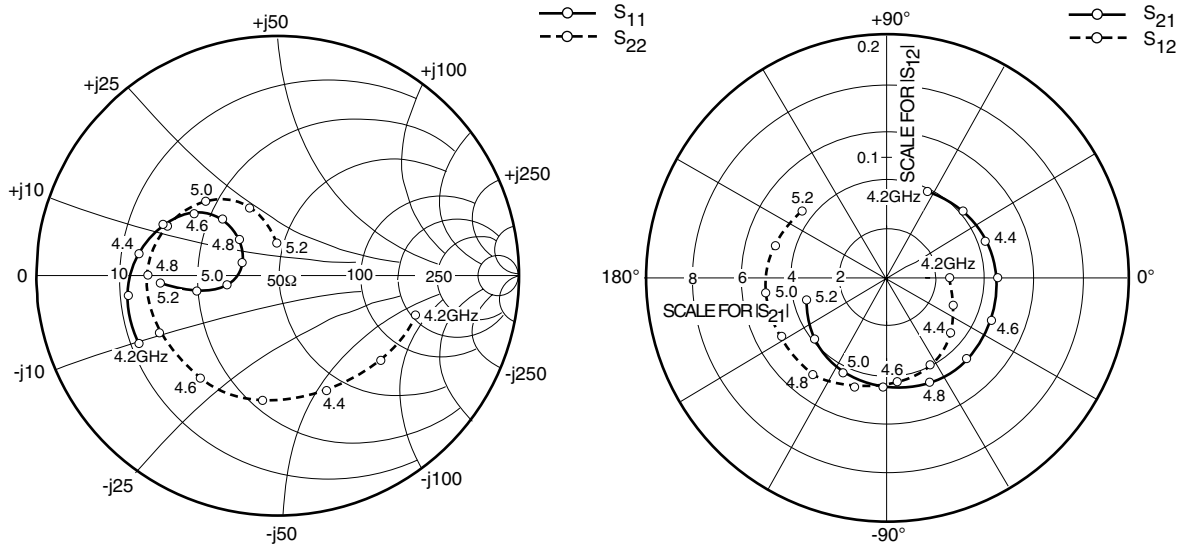


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER





S-PARAMETERS

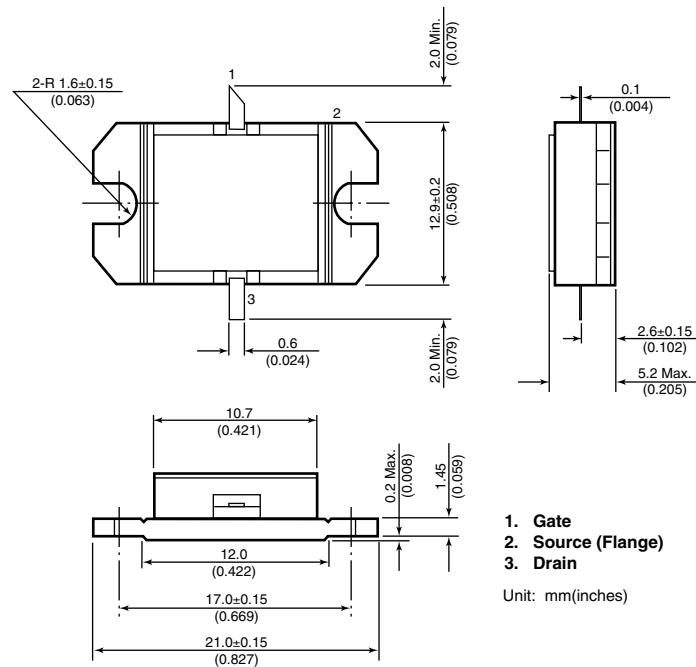
$V_{DS} = 10V, I_{DS} = 2200mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
4200	.645	-153.3	3.953	61.9	.051	-0.3	.592	-16.8
4300	.627	-171.7	4.154	41.9	.060	-22.2	.554	-40.3
4400	.578	171.7	4.326	21.1	.069	-40.4	.521	-67.5
4500	.520	156.4	4.501	-0.1	.079	-62.9	.521	-97.4
4600	.428	143.8	4.589	-22.2	.087	-84.8	.540	-127.0
4700	.325	134.2	4.642	-45.1	.095	-106.3	.550	-153.9
4800	.216	135.2	4.578	-68.2	.100	-127.1	.540	-179.7
4900	.158	160.9	4.434	-92.0	.100	-150.4	.504	156.1
5000	.214	-168.1	4.217	-116.1	.101	-172.5	.430	134.0
5100	.346	-167.2	3.892	-140.6	.096	164.6	.306	113.7
5200	.482	-175.7	3.469	-165.3	.089	141.9	.136	95.9

FLM4450-8F

C-Band Internally Matched FET

Case Style "IB" Metal-Ceramic Hermetic Package



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- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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